

Abstract

A method for fabricating a capacitor of a semiconductor device for improving a capacitance and concurrently enhancing a leakage current characteristic and a breakdown voltage characteristic. The method includes the steps of: (a) forming a conductive silicon layer for a bottom electrode on a substrate; (b) nitridating the conductive silicon layer; (c) oxidizing the nitridated conductive silicon layer; (d) forming a silicon nitride layer on a surface of the oxidized layer; (e) forming a dielectric layer on the silicon nitride layer; and (f) forming a top electrode on the dielectric layer.